HIGH FREQUENCY HIGH-SIDE AND LOW-SIDE GATE DRIVER IN V-QFN3030-8

Description

The DGD0590 is a high-frequency high-side and low-side gate driver capable of driving N-channel MOSFETs in a half-bridge configuration. The floating high-side driver is rated up to 50V and provides a 5V gate drive to the MOSFETs.

The DGD0590 logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with MCUs. A UVLO protects ICs and MOSFETs with loss of supply.

Fast and well-matched propagation delays allow a higher switching frequency, enabling a smaller, more compact power switching design, using smaller associated components. The DGD0590 is offered in the V-QFN3030-8 package and operates over an extended -40°C to +125°C temperature range.

Applications

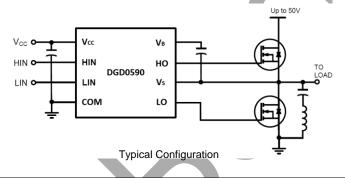
- Wireless Power Charger
- Motor Drive
- Logic Level MOSFET Gate Driver

Features

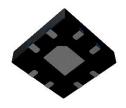
- 50V Floating High-Side Driver
- Low Vcc Operating Voltage: 4.5V to 5.5V
- Drives Two N-Channel Logic Level MOSFETs in a Half-Bridge Configuration
- High-Side 1.0A Source / 1.0A Sink and Low-Side 1.0A Source / 3.0A Sink Output Current Capability
- Internal Bootstrap Diode Included
- 3.4V UVLO with 0.4V Hysteresis
- Fast Rise and Fall Times (27ns/17ns) with 3nF Load
- Propagation Delay Typical of 16ns for High-Side and 12ns for
- Extended Temperature Range: -40°C to +125°C
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony free. "Green" Device (Note 3)

Mechanical Data

- Case: V-QFN3030-8 (Type TH)
- Case Material: Molded Plastic. "Green" Molding Compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals: Finish—Matte Tin Finish; Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.017 grams (Approximate)







Top View

Bottom View

V-QFN3030-8

Ordering Information (Note 4)

Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DGD0590FU-7	DGD0590	7	8	3000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information

Notes:

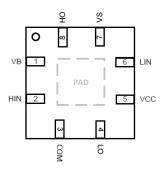


DGD0590 = Product Type Marking Code YY = Year (ex: 19 = 2019)WW = Week (01 to 53)





Pin Diagrams

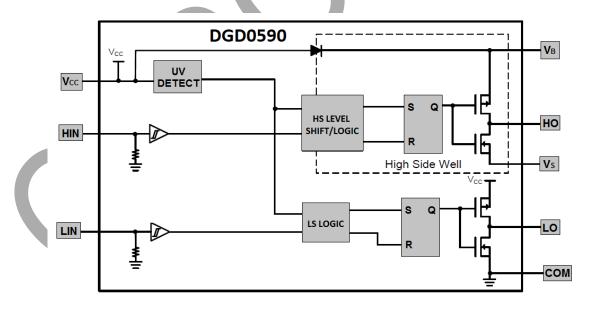


Top View: V-QFN3030-8

Pin Descriptions

Pin Number	Pin Name	Function
1	V_{B}	High-Side Floating Supply
2	HIN	Logic Input for High-Side Gate Driver, in Phase with HO, Pull Down Resistor at Input
3	COM	Low-Side and Logic Return
4	LO	Low-Side Gate Driver Output
5	Vcc	Low-Side and Logic Supply
6	LIN	Logic Input for Low-Side Gate Driver, in Phase with LO, Pull Down Resistor at Input
7	Vs	High-Side Floating Supply Return
8	НО	High-Side Gate Driver Output
PAD	Substrate	Connect to COM on PCB

Functional Block Diagram





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
High-Side Floating Positive Supply Voltage	V _B	0.3 to +60	V
High-Side Floating Negative Supply Voltage	Vs	V _B -6 to V _B +0.3	V
High-Side Floating Output Voltage	Vно	Vs-0.3 to V _B +0.3	V
Offset Supply Voltage Transient	dVs / dt	50	V/ns
Logic and Low-Side Fixed Supply Voltage	Vcc	-0.3 to +6	V
Low-Side Output Voltage	V _{LO}	-0.3 to V _{CC} +0.3	V
Logic Input Voltage (HIN and LIN)	Vin	-0.3 to +6	V

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Ambient (Note 5)	Reja	120	°C/W
Thermal Resistance, Junction to Case (Note 5)	Rejc	132	°C/W
Operating Temperature	TJ	+150	
Lead Temperature (Soldering, 10s)	TL	+300	°C
Storage Temperature Range	T _{STG}	-55 to +150	

Note: 5. When mounted on a standard JEDEC 2-layer FR-4 board.

Recommended Operating Conditions

Parameter	Symbol	Min	Max	Unit
High-Side Floating Supply	V _B	Vs + 4.5	V _S + 5.5	V
High-Side Floating Supply Offset Voltage	Vs	0	50 (Note 6)	V
High-Side Floating Output Voltage	Vно	Vs	VB	V
Logic and Low Side Fixed Supply Voltage	Vcc	4.5	5.5	V
Low-Side Output Voltage	V _{LO}	0	Vcc	V
Logic Input Voltage (HIN and LIN)	Vin	0	5	V
Ambient Temperature	T _A	-40	+125	°C

Note: 6. Provided V_B doesn't exceed absolute maximum rating of 60V.





DC Electrical Characteristics (V_{CC} = 5V, @T_A = +25°C, unless otherwise specified.)

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Logic "1" Input Voltage, HIN	VHIH	_	3.5	3.8	V	_
Logic "0" Input Voltage, HIN	V_{HIL}	1.0	1.3	_	V	_
Logic "1" Input Voltage, LIN	VLIH	_	2.8	3.3	V	_
Logic "0" Input Voltage, LIN	VLIL	1.0	1.2	_	V	_
Logic Input Bias Current	I _{IN+}	_	31	60	μA	VIN = VCC
Vcc Quiescent Supply Current	Iccq	_	22	50	μΑ	_
Vcc Operating Supply Current	Icco	_	300	_	μΑ	HO and LO Open, fs = 250kHz
High-Side Source Impedence	R _{HSO}	_	1.8	2.6	Ω	Source = 100mA
High-Side Sink Impedence	Rhsi	_	1.5	2.1	Ω	Sink = 100mA
Low-Side Source Impedence	Ruso	_	1.8	2.6	Ω	Source = 100mA
Low-Side Sink Impedence	R _{LSI}	_	0.4	1.0	Ω	Sink = 100mA
Vcc Supply Undervoltage Positive Going Threshold	Vccuv+	2.85	3.4	3.85	V	/
V _{CC} Supply Undervoltage Hysterisis	V _{CCU_HYST}	_	0.4	_	V	_
Bootstrap Diode Forward Voltage	V _{BFD}		650	800	mV	I = 100μA
Bootstrap Diode Reverse Leakage	I _{BDL}	_	0.1	0.4	μА	$V_B = V_S = 55.5V,$ $V_{CC} = 0V$

AC Electrical Characteristics (V_{CC} = 5V, C_L = 3nF, @T_A = +25°C, unless otherwise specified.)

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Turn-on Rise Time	tr	_	27	_	ns	_
Turn-off Fall Time, High-Side	1.		29	_	ns	_
Turn-off Fall Time, Low-Side	Lf Lf	-	17	_	ns	_
Turn-on Propagation Delay, High-Side	tonh		16	_	ns	_
Turn-off Propagation Delay, High-Side	toffh		17	_	ns	_
Turn-on Propagation Delay, Low-Side	tonl		12	_	ns	_
Turn-off Propagation Delay, Low-Side	toffl		17	_	ns	_





Timing Waveforms

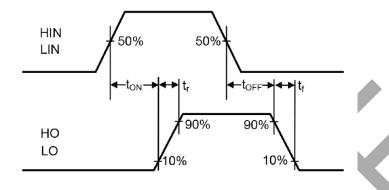


Figure 1. Switching Time Waveform Definitions

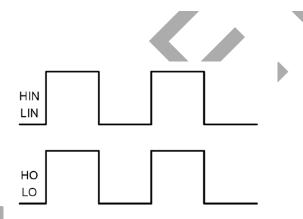


Figure 2. Input / Output Timing Diagram



Typical Performance Characteristics (Vcc = 5V, @TA = +25°C, unless otherwise specified.)

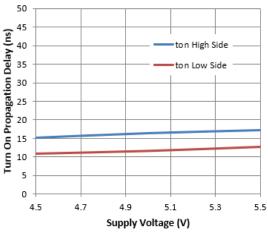


Figure 3. Turn-on Propagation Delay vs. Supply Voltage

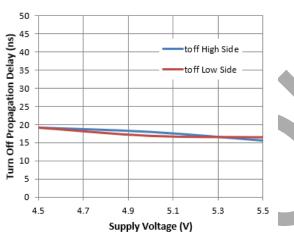


Figure 5. Turn-off Propagation Delay vs. Supply Voltage

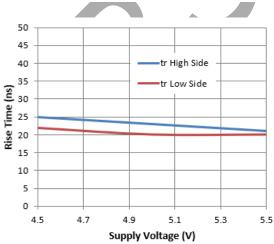


Figure 7. Rise Time vs. Supply Voltage

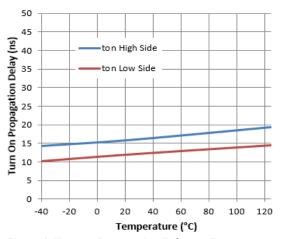


Figure 4. Turn-on Propagation Delay vs. Temperature

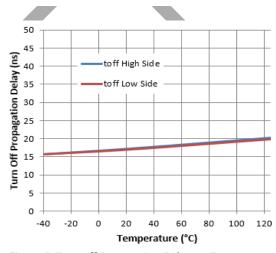


Figure 6. Turn-off Propagation Delay vs. Temperature

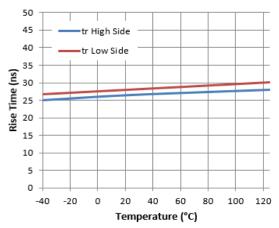


Figure 8. Rise Time vs. Temperature



Typical Performance Characteristics (continued)

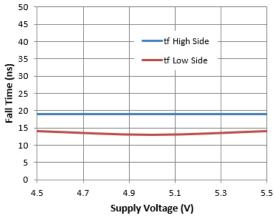


Figure 9. Fall Time vs. Supply Voltage

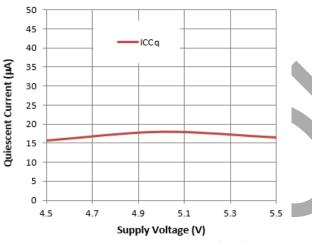


Figure 11. Quiescent Current vs. Supply Voltage

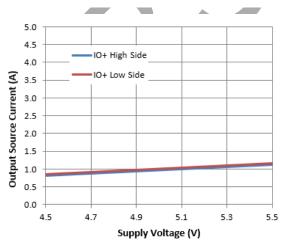


Figure 13. Output Source Current vs. Supply Voltage

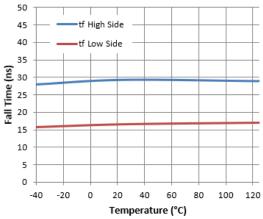


Figure 10. Fall Time vs. Temperature

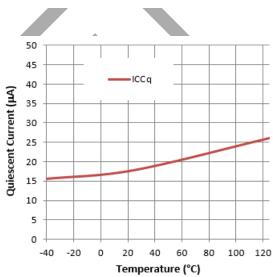


Figure 12. Quiescent Current vs. Temperature

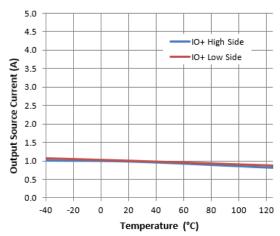


Figure 14. Output Source Current vs. Temperature



Typical Performance Characteristics (continued)

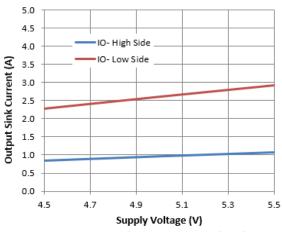


Figure 15. Output Sink Current vs. Supply Voltage

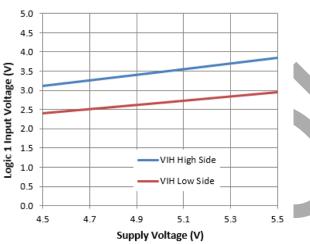


Figure 17. Logic 1 Input Voltage vs. Supply Voltage

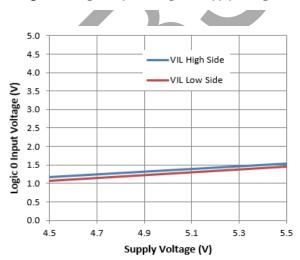


Figure 19. Logic 0 Input Voltage vs. Supply Voltage

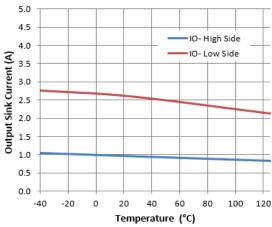


Figure 16. Output Sink Current vs. Temperature

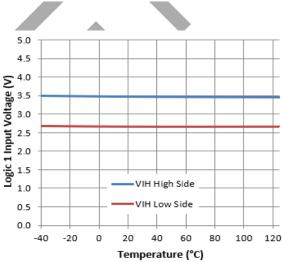


Figure 18. Logic 1 Input Voltage vs. Temperature

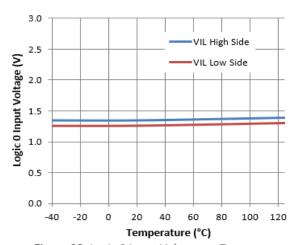


Figure 20. Logic 0 Input Voltage vs. Temperature



Typical Performance Characteristics (continued)

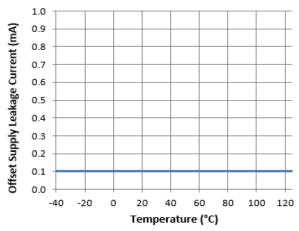


Figure 21. Offset Supply Leakage Current vs. Temperature

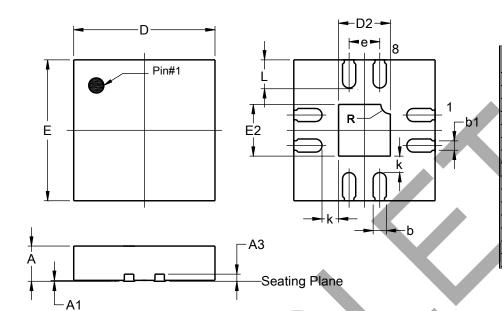




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

V-QFN3030-8 (Type TH)

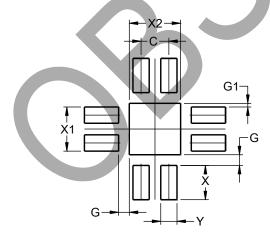


V-QFN3030-8						
(Type TH)						
Dim	Min Max Typ					
Α	0.70	0.80	0.75			
A1	0.00	0.05	0.02			
A3	O	0.203R	EF			
b	0.23	0.33	0.28			
b1		0.20R	Ξ F			
D	2.90	3.10	3.00			
D2	1.00	1.20	1.10			
Е	2.90	3.10	3.00			
E2	1.00	1.20	1.10			
е	0.65BSC					
Ы	0.55	0.65	0.60			
k	0.30	0.40	0.35			
R	0.20REF					
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

V-QFN3030-8 (Type TH)



Dimensions	Value (in mm)
С	0.650
G	0.250
G1	0.085
Х	0.800
X1	1.030
X2	1.200
٧	0 380



IMPORTANT NOTICE

- 1. DIODES INCORPORATED (Diodes) AND ITS SUBSIDIARIES MAKE NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO ANY INFORMATION CONTAINED IN THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).
- 2. The Information contained herein is for informational purpose only and is provided only to illustrate the operation of Diodes' products described herein and application examples. Diodes does not assume any liability arising out of the application or use of this document or any product described herein. This document is intended for skilled and technically trained engineering customers and users who design with Diodes' products. Diodes' products may be used to facilitate safety-related applications; however, in all instances customers and users are responsible for (a) selecting the appropriate Diodes products for their applications, (b) evaluating the suitability of Diodes' products for their intended applications, (c) ensuring their applications, which incorporate Diodes' products, comply the applicable legal and regulatory requirements as well as safety and functional-safety related standards, and (d) ensuring they design with appropriate safeguards (including testing, validation, quality control techniques, redundancy, malfunction prevention, and appropriate treatment for aging degradation) to minimize the risks associated with their applications.
- 3. Diodes assumes no liability for any application-related information, support, assistance or feedback that may be provided by Diodes from time to time. Any customer or user of this document or products described herein will assume all risks and liabilities associated with such use, and will hold Diodes and all companies whose products are represented herein or on Diodes' websites, harmless against all damages and liabilities.
- 4. Products described herein may be covered by one or more United States, international or foreign patents and pending patent applications. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks and trademark applications. Diodes does not convey any license under any of its intellectual property rights or the rights of any third parties (including third parties whose products and services may be described in this document or on Diodes' website) under this document.
- 5. Diodes' products are provided subject to Diodes' Standard Terms and Conditions of Sale (https://www.diodes.com/about/company/terms-and-conditions-of-sales/) or other applicable terms. This document does not alter or expand the applicable warranties provided by Diodes. Diodes does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.
- 6. Diodes' products and technology may not be used for or incorporated into any products or systems whose manufacture, use or sale is prohibited under any applicable laws and regulations. Should customers or users use Diodes' products in contravention of any applicable laws or regulations, or for any unintended or unauthorized application, customers and users will (a) be solely responsible for any damages, losses or penalties arising in connection therewith or as a result thereof, and (b) indemnify and hold Diodes and its representatives and agents harmless against any and all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim relating to any noncompliance with the applicable laws and regulations, as well as any unintended or unauthorized application.
- 7. While efforts have been made to ensure the information contained in this document is accurate, complete and current, it may contain technical inaccuracies, omissions and typographical errors. Diodes does not warrant that information contained in this document is error-free and Diodes is under no obligation to update or otherwise correct this information. Notwithstanding the foregoing, Diodes reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes.
- 8. Any unauthorized copying, modification, distribution, transmission, display or other use of this document (or any portion hereof) is prohibited. Diodes assumes no responsibility for any losses incurred by the customers or users or any third parties arising from any such unauthorized
- 9. This Notice may be periodically updated with the most recent version available at https://www.diodes.com/about/company/terms-and-conditions/important-notice

The Diodes logo is a registered trademark of Diodes Incorporated in the United States and other countries. All other trademarks are the property of their respective owners.

© 2024 Diodes Incorporated. All Rights Reserved.

www.diodes.com